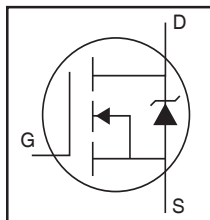


HEXFET® Power MOSFET

Applications

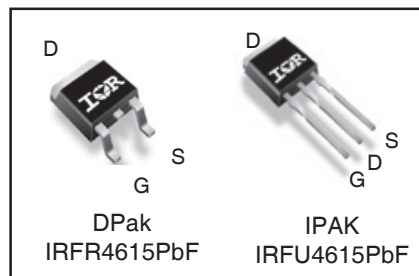
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits



V_{DSS}		150V
$R_{DS(on)}$	typ.	34mΩ
	max.	42mΩ
I_D		33A

Benefits

- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free



G	D	S
Gate	Drain	Source

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFR4615PbF	D-PAK	Tube/Bulk	75	IRFR4615PbF
IRFR4615TRLPbF		Tape and Reel Left	3000	IRFR4615TRLPbF
IRFU4615PbF	I-PAK	Tube/Bulk	75	IRFU4615PbF

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	33	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	24	
I_{DM}	Pulsed Drain Current ①	140	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	144	W
	Linear Derating Factor	0.96	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery ③	38	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Avalanche Characteristics

E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	109	mJ
I_{AR}	Avalanche Current ①	See Fig. 14, 15, 22a, 22b,	A
E_{AR}	Repetitive Avalanche Energy ①		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ③	—	1.045	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ②	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

Notes ① through ③ are on page 11

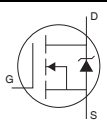
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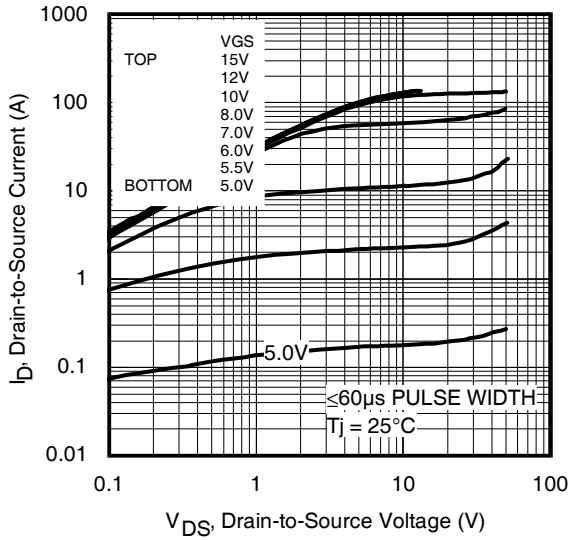
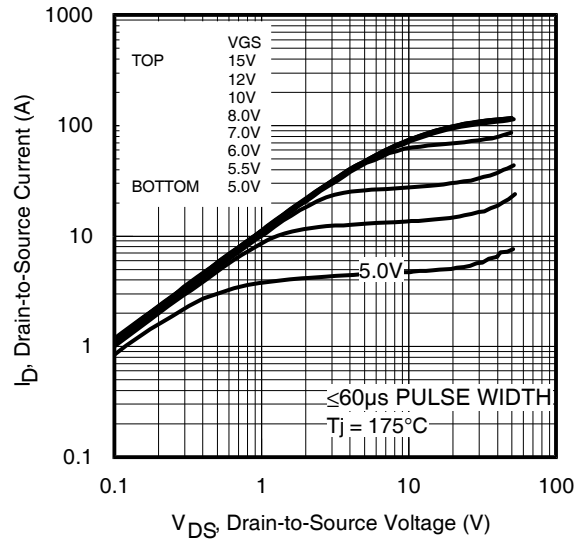
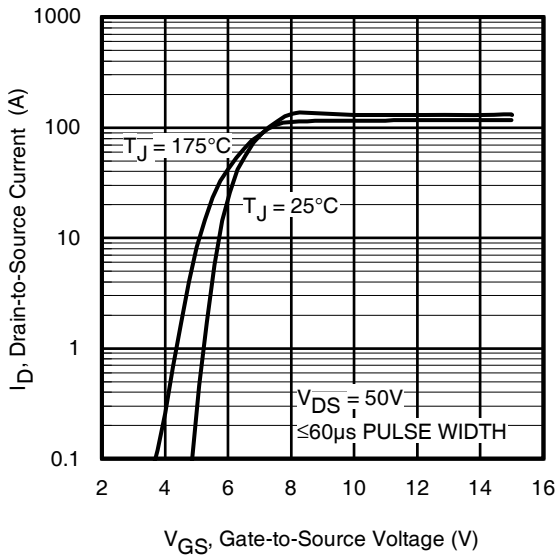
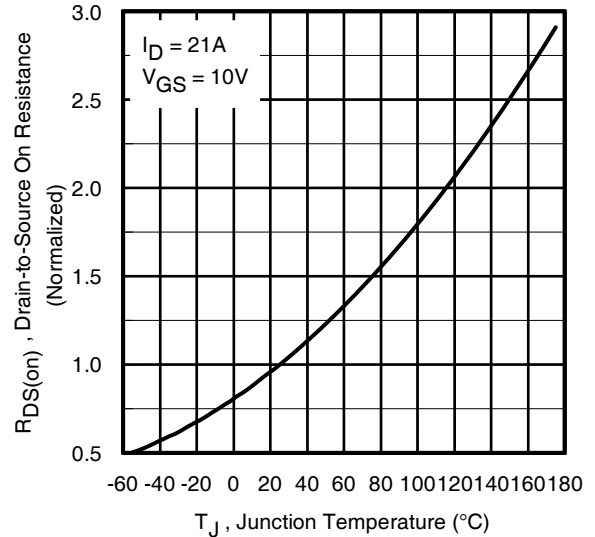
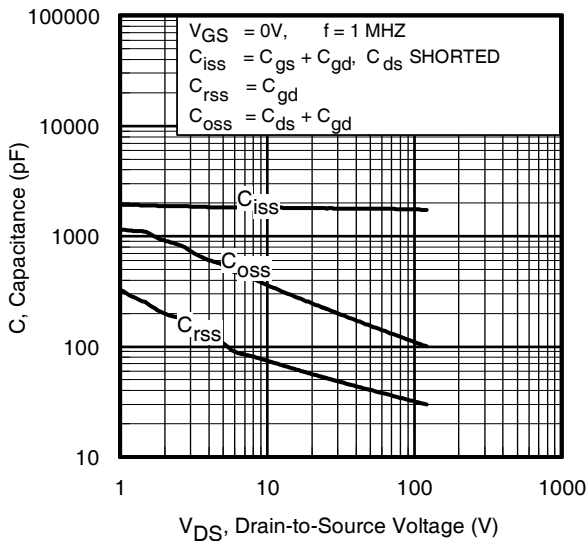
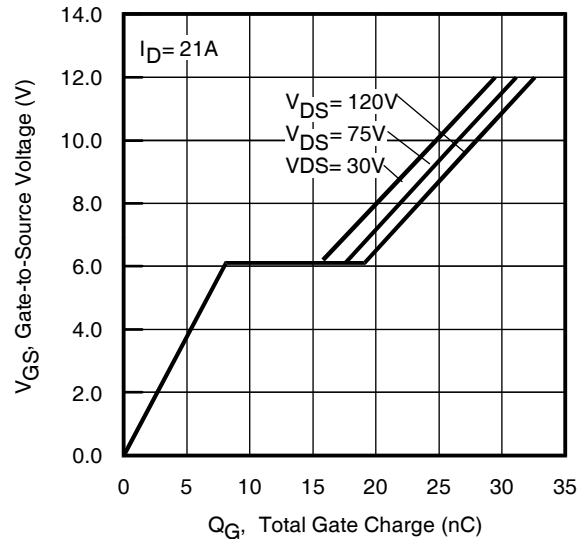
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	150	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.19	—	V/°C	Reference to 25°C, I _D = 5mA ^①
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	34	42	mΩ	V _{GS} = 10V, I _D = 21A ^④
V _{GS(th)}	Gate Threshold Voltage	3.0	—	5.0	V	V _{DS} = V _{GS} , I _D = 100μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	V _{DS} = 150V, V _{GS} = 0V
		—	—	250		V _{DS} = 150V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
R _{G(int)}	Internal Gate Resistance	—	2.7	—	Ω	

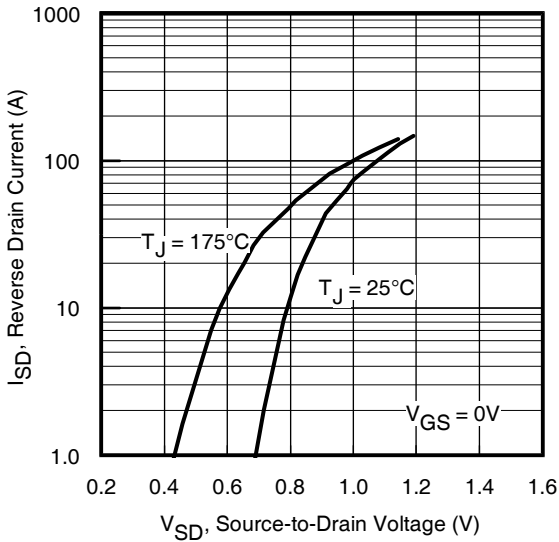
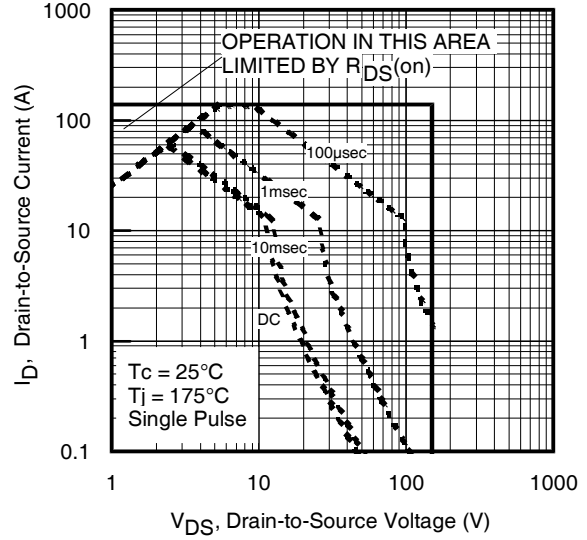
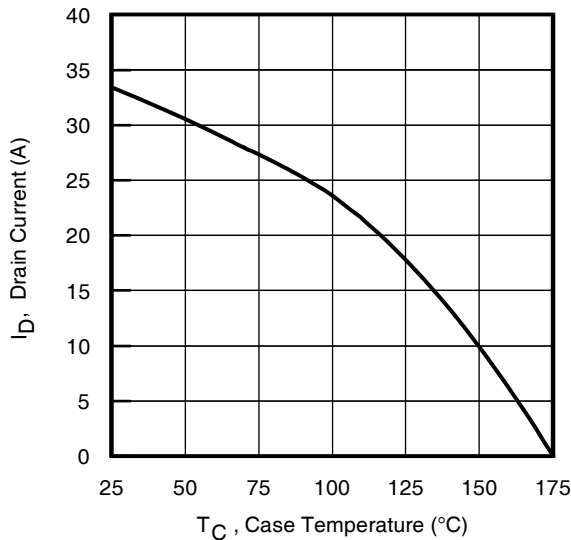
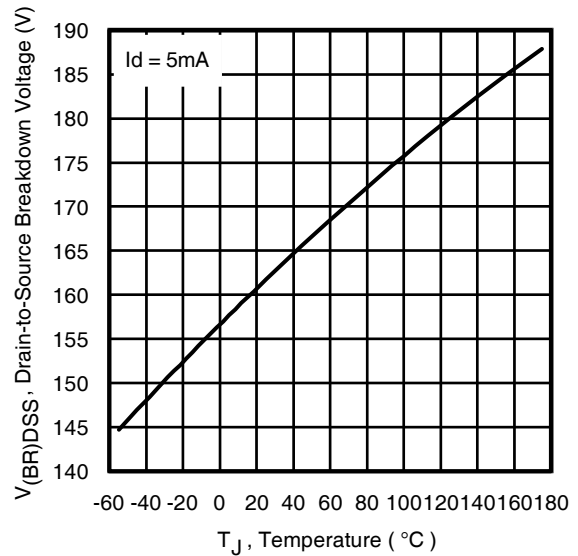
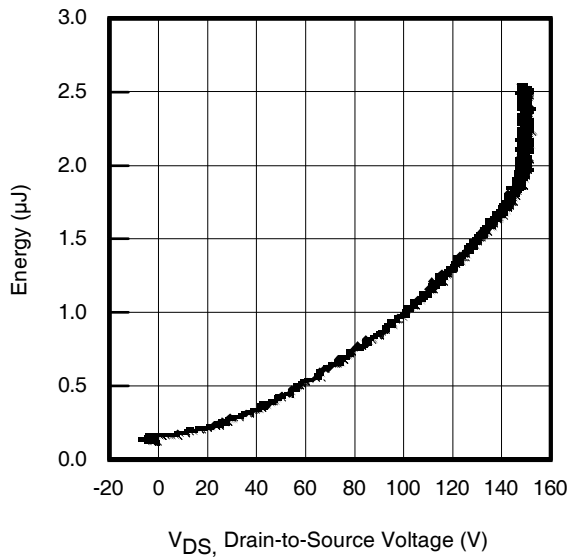
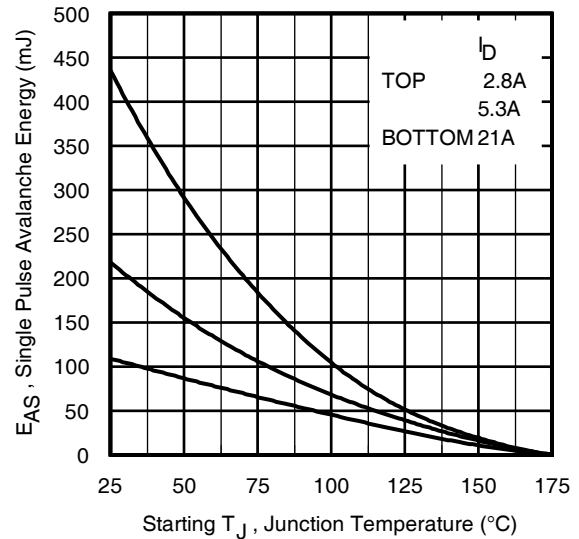
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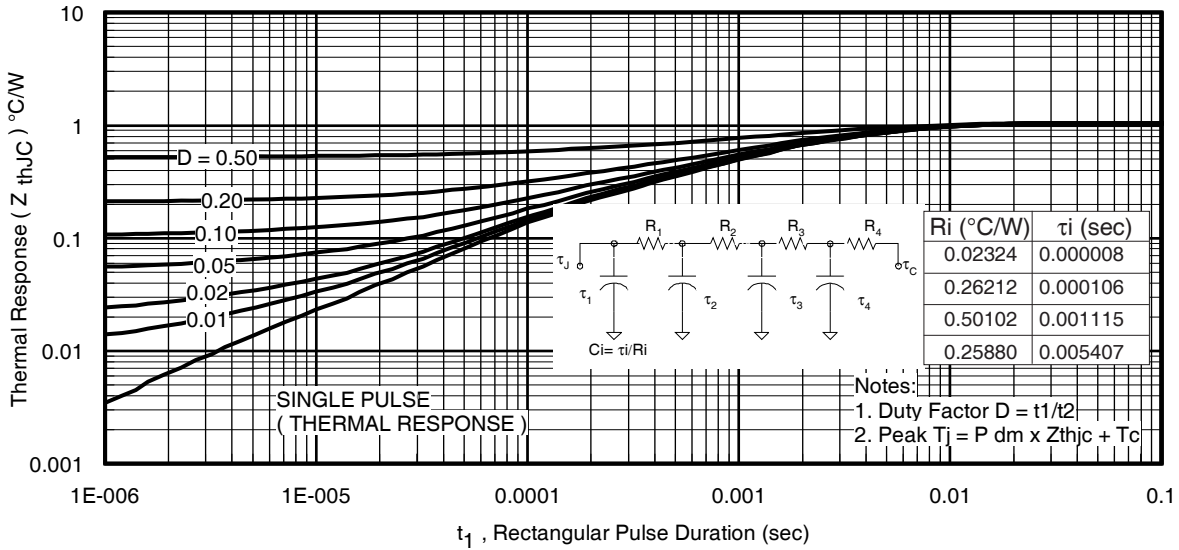
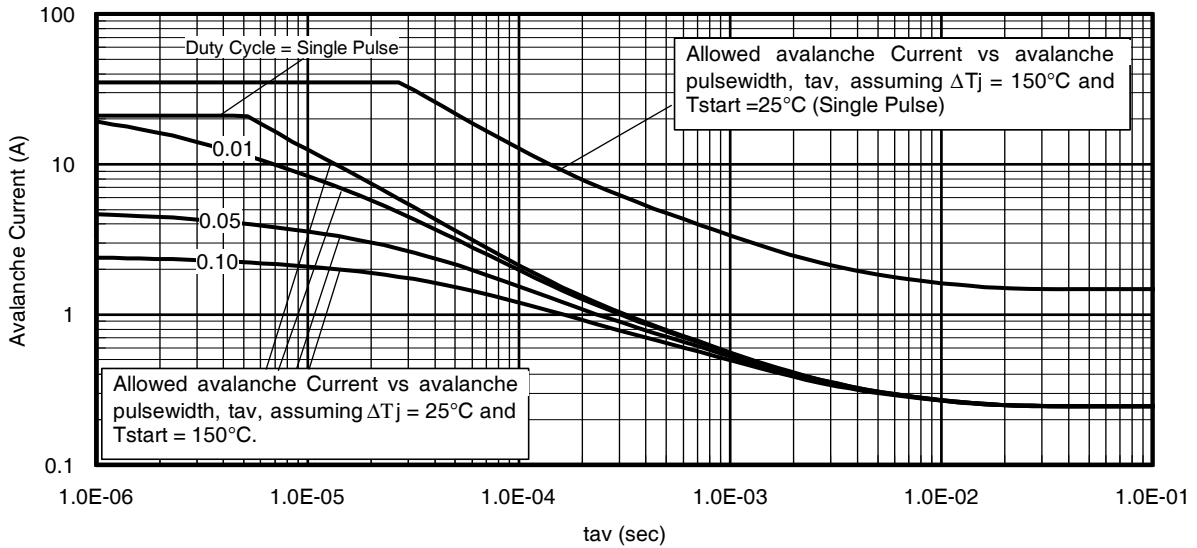
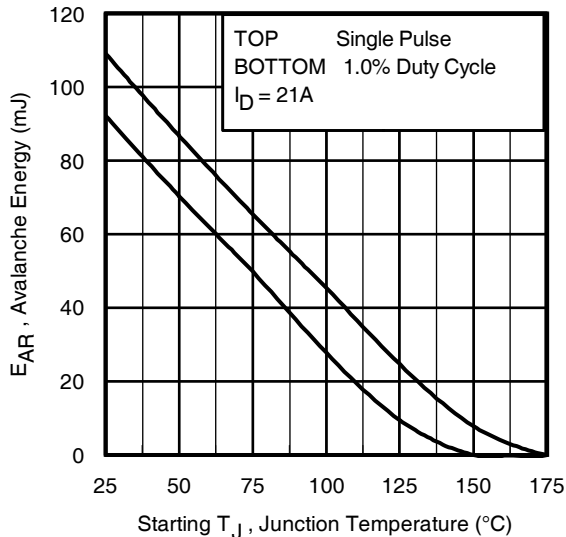
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	35	—	—	S	V _{DS} = 50V, I _D = 21A
Q _g	Total Gate Charge	—	26	—	nC	I _D = 21A
Q _{gs}	Gate-to-Source Charge	—	8.6	—		V _{DS} = 75V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	9.0	—		V _{GS} = 10V ^④
Q _{sync}	Total Gate Charge Sync. (Q _g - Q _{gd})	—	17	—		I _D = 21A, V _{DS} = 0V, V _{GS} = 10V
t _{d(on)}	Turn-On Delay Time	—	15	—	ns	V _{DD} = 98V
t _r	Rise Time	—	35	—		I _D = 21A
t _{d(off)}	Turn-Off Delay Time	—	25	—		R _G = 7.3Ω
t _f	Fall Time	—	20	—		V _{GS} = 10V ^④
C _{iss}	Input Capacitance	—	1750	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	155	—		V _{DS} = 50V
C _{rss}	Reverse Transfer Capacitance	—	40	—		f = 1.0MHz (See Fig.5)
C _{oss eff. (ER)}	Effective Output Capacitance (Energy Related) ^⑥	—	179	—		V _{GS} = 0V, V _{DS} = 0V to 120V ^⑥ (See Fig.11)
C _{oss eff. (TR)}	Effective Output Capacitance (Time Related) ^⑤	—	382	—		V _{GS} = 0V, V _{DS} = 0V to 120V ^⑤

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	33	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ^①	—	—	140		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 21A, V _{GS} = 0V ^④
t _{rr}	Reverse Recovery Time	—	70	—	ns	T _J = 25°C V _R = 100V,
		—	83	—		T _J = 125°C I _F = 21A
Q _{rr}	Reverse Recovery Charge	—	177	—	nC	T _J = 25°C di/dt = 100A/μs ^④
		—	247	—		T _J = 125°C
I _{RRM}	Reverse Recovery Current	—	4.9	—	A	T _J = 25°C
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage


Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10. Drain-to-Source Breakdown Voltage

Fig 11. Typical C_{OSS} Stored Energy

Fig 12. Maximum Avalanche Energy vs. Drain Current


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig 14. Typical Avalanche Current vs. Pulsewidth

**Notes on Repetitive Avalanche Curves, Figures 14, 15:
 (For further info, see AN-1005 at www.irf.com)**

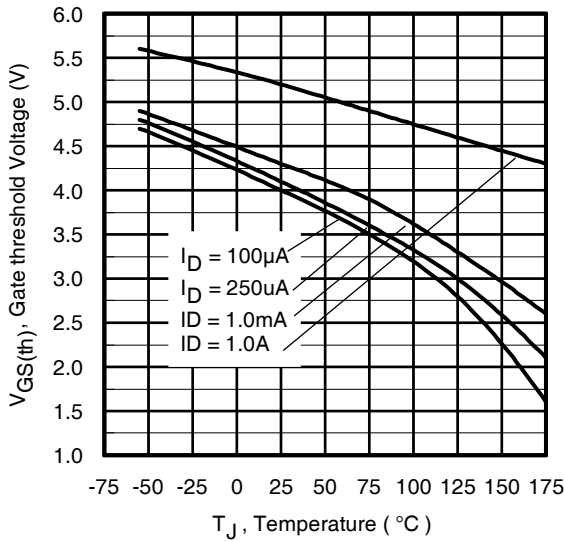
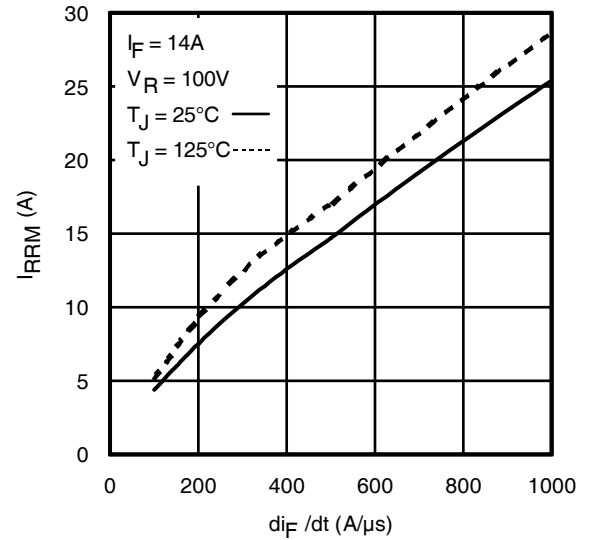
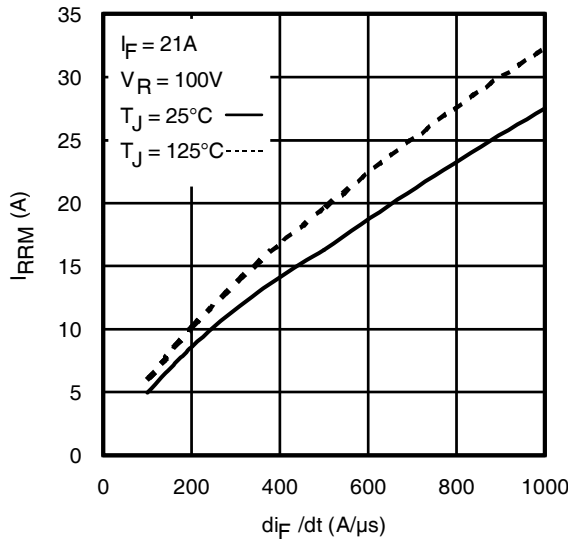
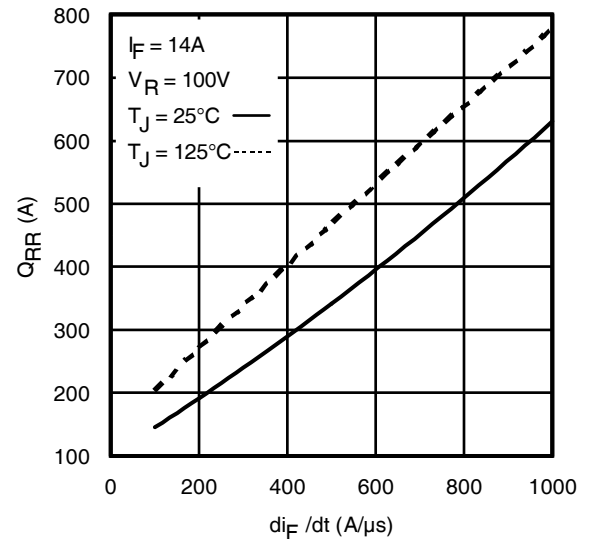
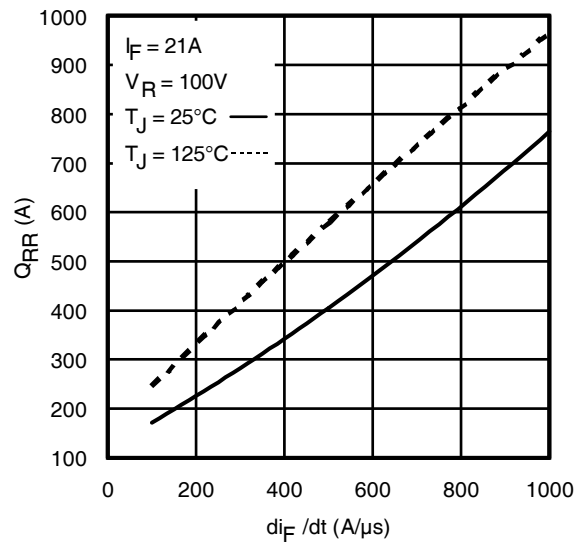
1. Avalanche failures assumption:
 Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

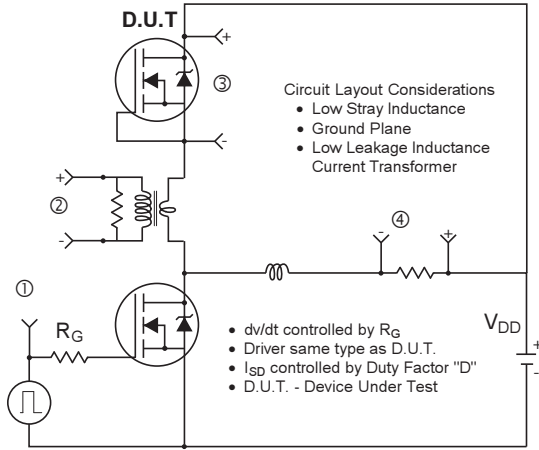
$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

Fig 15. Maximum Avalanche Energy vs. Temperature


Fig. 16. Threshold Voltage vs. Temperature

Fig. 17 - Typical Recovery Current vs. di_F/dt

Fig. 18 - Typical Recovery Current vs. di_F/dt

Fig. 19 - Typical Stored Charge vs. di_F/dt

Fig. 20 - Typical Stored Charge vs. di_F/dt



* $V_{GS} = 5V$ for Logic Level Devices

Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

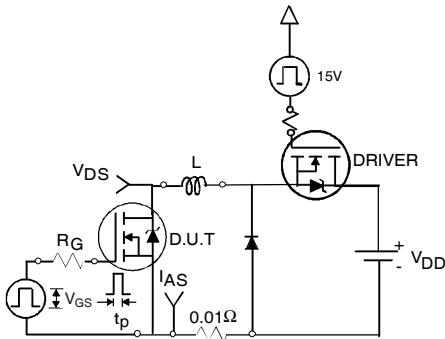


Fig 22a. Unclamped Inductive Test Circuit

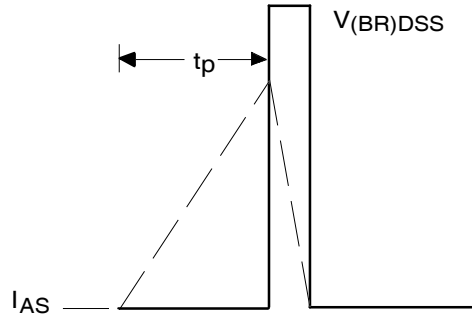


Fig 22b. Unclamped Inductive Waveforms

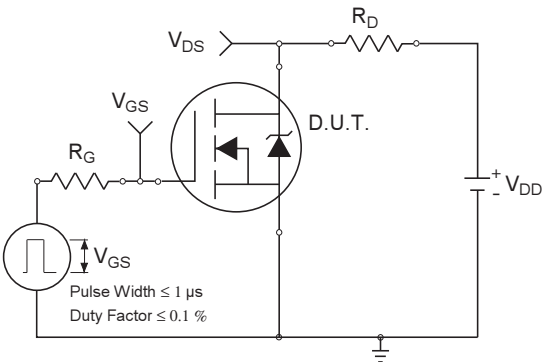


Fig 23a. Switching Time Test Circuit

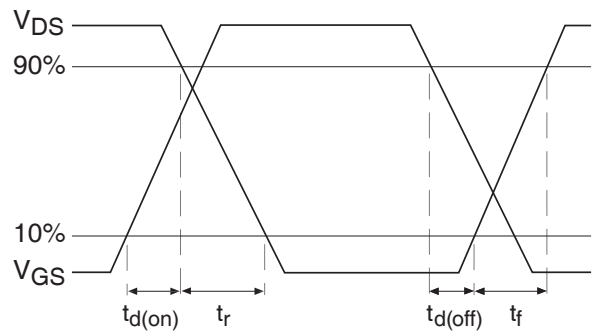


Fig 23b. Switching Time Waveforms

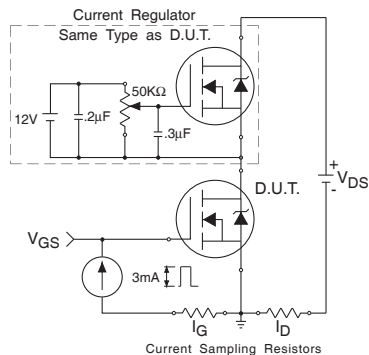


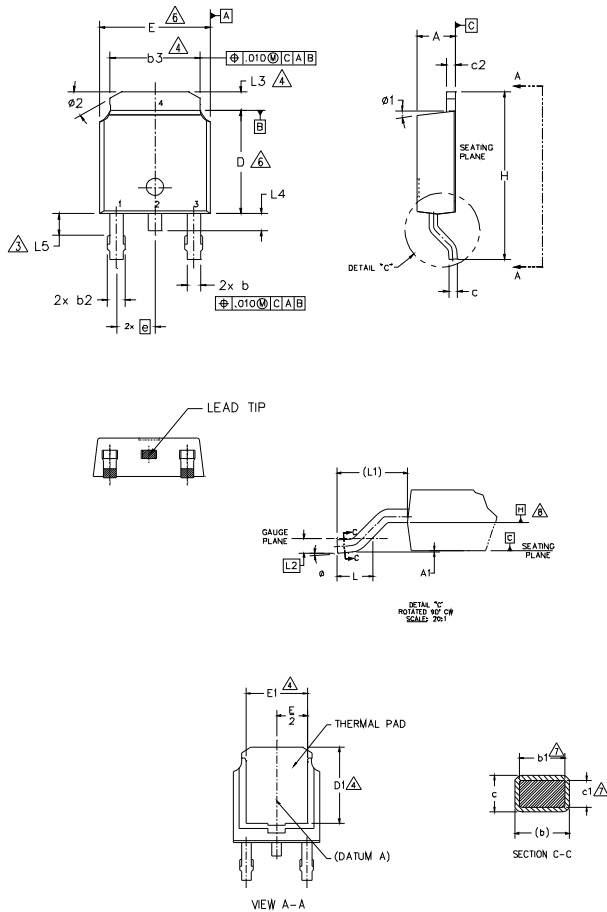
Fig 24a. Gate Charge Test Circuit



Fig 24b. Gate Charge Waveform

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 - 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
 - 3.- LEAD DIMENSION UNCONTROLLED IN L5.
 - 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
 - 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
 - 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 - 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
 - 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 - 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	
ø2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

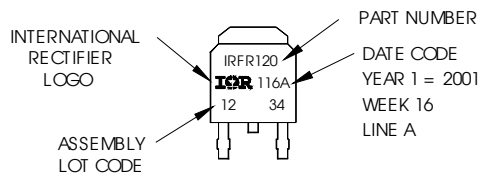
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120 WITH ASSEMBLY LOT CODE 1234 ASSEMBLED ON WW 16, 2001 IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates "Lead-Free"

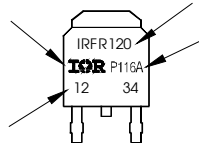
"P" in assembly line position indicates "Lead-Free" qualification to the consumer-level



OR

INTERNATIONAL RECTIFIER LOGO

ASSEMBLY LOT CODE



PART NUMBER

DATE CODE
P = DESIGNATES LEAD-FREE PRODUCT (OPTIONAL)

P̄ = DESIGNATES LEAD-FREE PRODUCT QUALIFIED TO THE CONSUMER LEVEL (OPTIONAL)

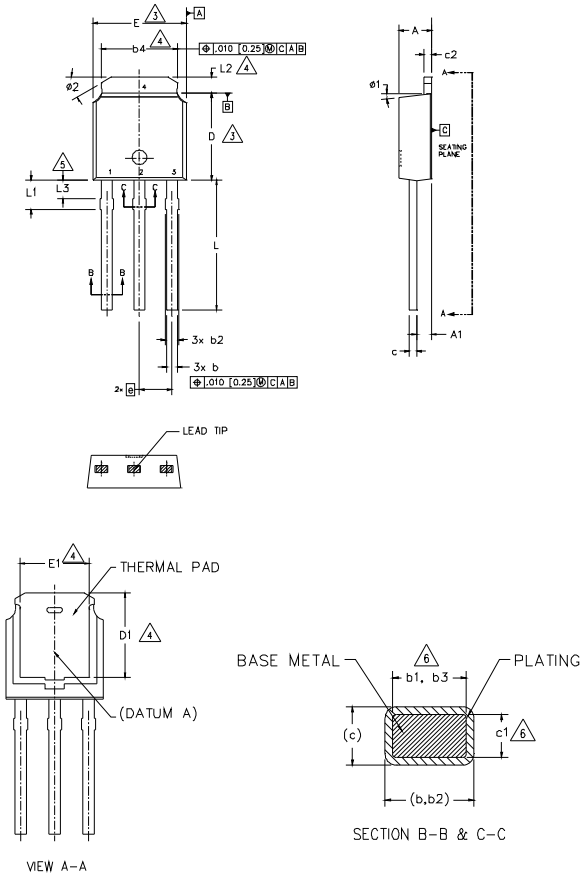
YEAR 1 = 2001
WEEK 16

A = ASSEMBLY SITE CODE

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 4.- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5.- LEAD DIMENSION UNCONTROLLED IN L3.
- 6.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
- 8.- CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	0.89	1.14	.035	.045	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	6
b2	0.76	1.14	.030	.045	
b3	0.76	1.04	.030	.041	6
b4	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	6
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	3
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	3
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
L	8.89	9.65	.350	.380	
L1	1.91	2.29	.045	.090	
L2	0.89	1.27	.035	.050	4
L3	1.14	1.52	.045	.060	5
Ø1	0"	15"	0"	15"	
Ø2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

HEXFET

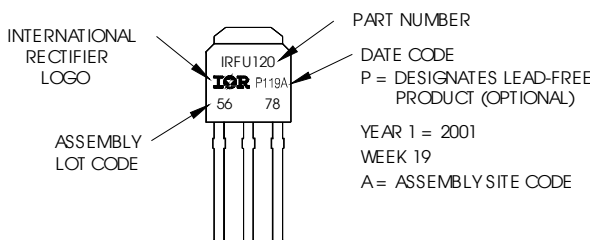
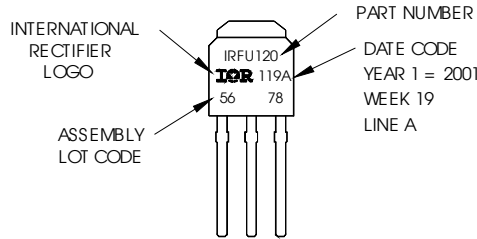
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120 WITH ASSEMBLY LOT CODE 5678 ASSEMBLED ON WW19, 2001 IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates Lead-Free!

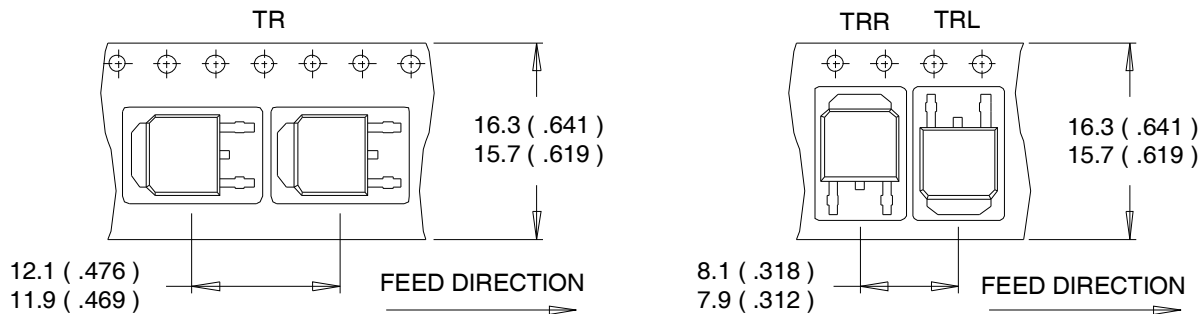
OR



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

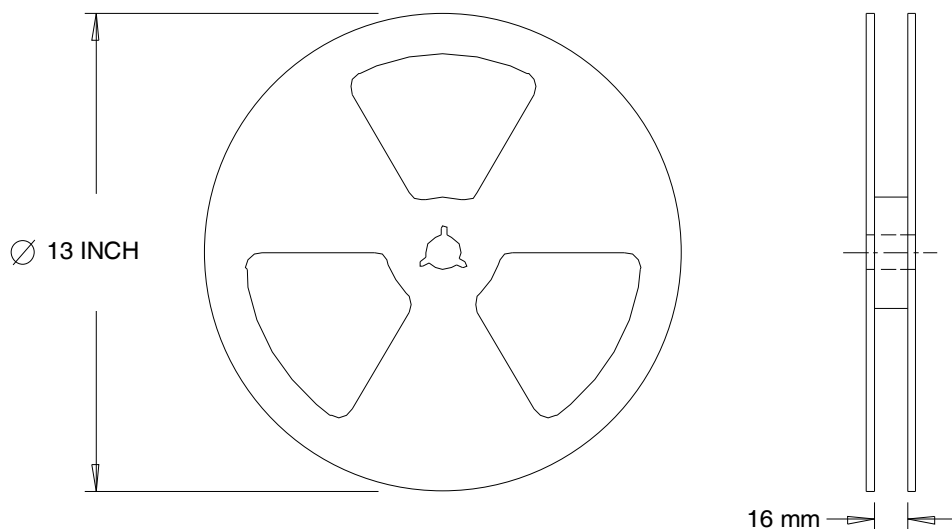
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information†

Qualification level	Industrial (per JEDEC JESD47F ^{††} guidelines)	
Moisture Sensitivity Level	D-PAK	MSL1 (per JEDEC J-STD-020D ^{††})
	I-PAK	Not applicable
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site <http://www.irf.com/product-info/reliability>

†† Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax} , starting $T_J = 25^\circ C$, $L = 0.51mH$
 $R_G = 25\Omega$, $I_{AS} = 21A$, $V_{GS} = 10V$. Part not recommended for use above this value .
- ③ $I_{SD} \leq 21A$, $di/dt \leq 549A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ C$.
- ④ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ⑤ C_{OSS} eff. (TR) is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ C_{OSS} eff. (ER) is a fixed capacitance that gives the same energy as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994
- ⑧ R_θ is measured at T_J approximately $90^\circ C$

Revision History

Date	Comments
5/16/2013	<ul style="list-style-type: none"> • Updated datasheet to new IR corporate formatting template • Updated Orderable part number from "IRFR4615TRPbF" to "IRFR4615TRLpBf", on page 1

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